



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of)
Kichiya TANINO et al) Art Unit: 1765
Appln. No.: 09/771,556) Ex: R.M. Kunemund
Filed: January 30, 2001)
For: SINGLE CRYSTAL SiC AND A)
METHOD OF GROWING THE SAME)

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RESPONSE TO FURTHER NOTICE OF NON-COMPLIANT AMENDMENT
(37 CFR 1.121)

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

The following amendments to the specification are being submitted in response to the Further Notice of Non-Compliant Amendment (37 CFR 1.121) dated August 28, 2002.

AMENDMENT

IN THE SPECIFICATION:

Please replace the paragraphs beginning on line 12 on page 4 to page 7, first 4 lines with the following:

C₁
--In order to attain the above-mentioned object, the single crystal SiC according to a first aspect of the invention is characterized in that heat treatment is performed in an inert gas atmosphere under a state where a cutting plane of a single crystal α -SiC substrate which is formed by cutting along $(1, 1, \bar{2}, 0)$ Miller index plane $\pm 10^\circ$, and $(2, 2, 0)$ Miller index plane of a polycrystalline β -SiC plate are superimposed on each other, whereby single crystal having a